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## Patent Abstracts of Japan

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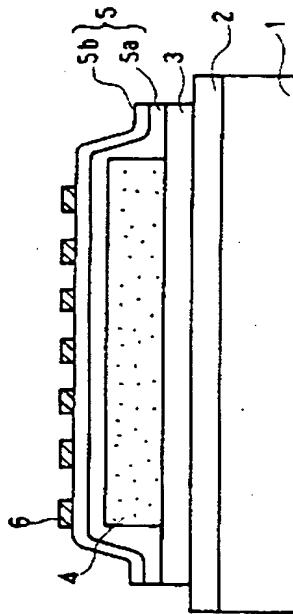
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TITLE : THIN FILM ELECTROLUMINESCENT DEVICE



**ABSTRACT :** PURPOSE: To obtain a thin film electroluminescent device with high luminance and high reliability by using AlN for the first insulating layer and a layer, whose host material is C-axis-oriented ZnO, for a transparent electrode, in an electroluminescent device using a luminescent layer whose host material is alkaline earth chalcogenide.

CONSTITUTION: In an electroluminescent device using a luminescent layer 4 whose host material is alkaline earth chalcogenide, ZnO, which is doped with A1, Si, or the like as a host material, is used for a transparent electrode 2. C-axis-oriented ZnO is especially used for the ZnO layer. The first insulating material 3 is composed of two or more layers, for one of which adjacent to the luminescent layer 4 crystalline aluminum nitride AlN or crystalline boron nitride BN is used. Though non-crystalline layers are generally used for insulating layers, polycrystal or single crystal is used for AlN. Polycrystalline AlN and BN have high dielectric strength and especially in case that they are used for electroluminescent devices, the dielectric strength of the devices can therefore be enhanced.

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